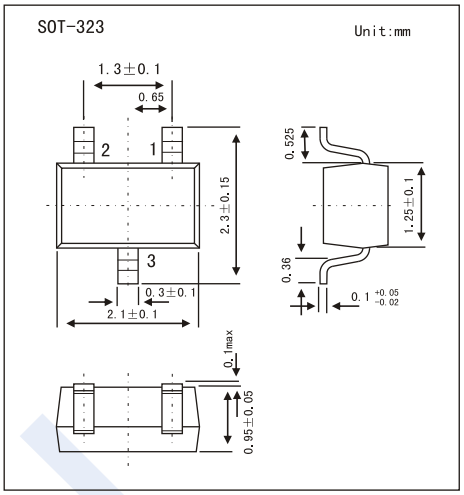
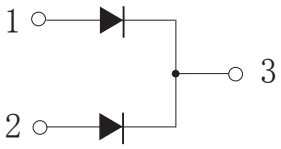
Schottky Diodes

RB715F (KB715F)



■ Features

- Extra small power mold type
- Low V_F
- High reliability



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Peak Reverse Voltage	V_{RM}	40	V
DC Reverse Voltage	V_R	40	
Average Forward Current	I_O	30	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	200	
Power Dissipation	P_d	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	500	℃/W
Junction Temperature	T_J	125	℃
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	I_R= 100 uA	40			V
Forward voltage	V_F	I_F= 1 mA			0.37	
Reverse voltage leakage current	I_R	V_R= 10 V			1	uA
Junction capacitance	C_j	V_R= 1 V, f= 1 MHz		2		pF

■ Marking

Marking	3D

Schottky Diodes

RB715F (KB715F)

■ Typical Characterisitics